

Single Crystal Perovskites Analyzed Using X-ray Photoelectron Spectroscopy: 5. NdGaO₃(110)

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Citation: [Surface Science Spectra](#) **21**, 122 (2014); doi: 10.1116/11.20140905

View online: <http://dx.doi.org/10.1116/11.20140905>

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Single Crystal Perovskites Analyzed Using X-ray Photoelectron Spectroscopy: 5. NdGaO₃(110)

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(Received 3 October 2014; accepted 4 December 2014; published 31 December 2014)

X-ray photoelectron spectroscopy (XPS) was used to analyze a commercially available NdGaO₃ (110) bulk single crystal. XP spectra were obtained using incident monochromatic Al K_α radiation at 0.83401 nm. A survey spectrum together with Ga 2p, Nd 3d, O 1s, C 1s, Nd 4p_{3/2}, Ga 3s, Nd 4d, Ga 3p, Nd 5s, O 2s, Ga 3d and Nd 5p core level spectra and the valence band are presented. The spectra indicate the principle core level photoelectron and Auger electron signals and show only minor carbon contamination. Making use of the O 1s, Nd 4d, Ga 3p lines and neglecting the components related to surface contaminants, XPS quantitative analysis reveals an altered stoichiometry of the air-exposed crystal surface of Nd_{1.13}GaO_{2.17}. © 2014 American Vacuum Society. [<http://dx.doi.org/10.1116/11.20140905>]

Keywords: neodymium gallium oxide; perovskite

INTRODUCTION

Transition metal oxides present an impressive variety of functionality which is not available in more traditional systems such as group IV and III-V semiconductors or elemental metals. Among the many possible functionalities are, for instance, ferroelectricity (Ref. 1) and magnetism (Ref. 2), colossal magnetoresistance (Ref. 3), and high temperature superconductivity (Ref. 4), with transport character ranging from insulating to semiconducting to metallic. Furthermore, these properties are extremely sensitive to perturbations from chemistry, structural defects, strain and many other effects and this, in turn, provides the materials engineer a number of routes by which to engineer new functionalities in this class of materials (Ref. 5). While even simple oxide systems, such as binary oxides, exhibit a broad diversity of properties, it is the ternary systems which have received the most attention in recent years. In particular, materials possessing the perovskite structure (with chemical formula ABO₃) have been observed to exhibit an incredible variety of functionality and phenomena. Advances in thin film epitaxy, particularly pulsed laser deposition, RF magnetron sputtering, and molecular beam epitaxy, have enabled researchers to carefully tune material properties using epitaxial strain. Such approaches have provided an opportunity to apply large biaxial strains (as much as several percent in some cases) to nanoscale films of various materials which would lead to cracks in bulk materials under similar values of hydrostatic strain (Ref. 6).

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SPECIMEN DESCRIPTION (ACCESSION #01314)

Host Material: Single crystal NdGaO₃

CAS Registry #: 12207-22-6

Host Material Characteristics: homogeneous; solid; single crystal; dielectric; inorganic compound

Chemical Name: Neodymium gallium oxide

Source: Crystec, GmbH. Grown by the Czochralski method.

Host Composition: NdGaO₃

Form: single crystal

Structure: orthorhombically distorted perovskite-type structure, Pbnm, Z = 4 (Ref. 7)

History & Significance: NdGaO₃ has been widely used as a designed substrate for a number of important applications. It originally rose to prominence as a competitive substrate for high TC oxide superconductors due to its low dielectric response, exceptional crystallinity, cubic symmetry, and small lattice constant (Ref. 8). Since then, it has been used as an epitaxial substrate for ferroelectric materials (Ref. 9), high-quality optoelectronic semiconductors (Ref. 10), and colossal magnetoresistive materials (Ref. 11). In order to gain an increased understanding of the surfaces and hetero-interfaces of perovskite-based materials, NdGaO₃ bulk single crystal was analyzed using X-ray photoelectron spectroscopy.

As Received Condition: as grown

Analyzed Region: same as host material

Accession #: 01314

Technique: XPS

Host Material: Single crystal NdGaO₃

Instrument: Kratos Axis Ultra

Major Elements in Spectra: Nd, Ga, O

Minor Elements in Spectra: C

Published Spectra: 9

Spectra in Electronic Record: 9

Spectral Category: comparison

Ex Situ Preparation/Mounting: Samples were cleaned ultrasonically for 5 min each in Formula 409[®], methyl alcohol, and deionized water. Samples were mounted onto the sample holder using double-sided carbon tape (Pella product number 16074).

In Situ Preparation: None

Pre-Analysis Beam Exposure: less than 2 min; no x-ray degradation effects observed

Charge Control: low energy flood gun/magnetic immersion lens combination, filament current = 1.8 A, charge balance = 3 V, filament bias = 1 V

Temp. During Analysis: 300 K

Pressure During Analysis: $<3 \times 10^{-7}$ Pa

INSTRUMENT DESCRIPTION

Manufacturer and Model: Kratos Axis Ultra

Analyzer Type: spherical sector

Detector: channeltron electron multiplier

Number of Detector Elements: 8

INSTRUMENT PARAMETERS COMMON TO ALL SPECTRA —

■ Spectrometer

Analyzer Mode: constant pass energy

Throughput ($T = E^M$): $N = 0$

Excitation Source Window: not specified

Excitation Source: Al K_{α} , monochromatic

Source Energy: 1486.6 eV

Source Strength: 180 W

Source Beam Size: $2000 \mu\text{m} \times 2000 \mu\text{m}$

Signal Mode: multichannel direct

■ Geometry

Incident Angle: 54°

Source to Analyzer Angle: 54°

Emission Angle: 0°

Specimen Azimuthal Angle: 45°

Acceptance Angle from Analyzer Axis: 0°

Analyzer Angular Acceptance Width: $40^\circ \times 40^\circ$

DATA ANALYSIS METHOD

Energy Scale Correction: The binding energy scale was referenced to C 1s = 285.0 eV.

Recommended Energy Scale Shift: +2.071 eV for high-resolution spectra

Peak Shape and Background Method: Background: Custom three parameter Tougaard background (Ref. 12), U 4 Tougaard (B, C, D, T0 = 0) (Ref. 13), was used. O 1s, C 1s, Nd 4d, Ga 3p: B = 299 eV², C = 542 eV², D = 275 eV².

Quantitation Method: Quantification was done using region and component definitions with CasaXPS version 2.3.15. Sensitivity factors were supplied by Kratos Analytical. Errors are given as ± 1 standard deviation. Standard deviations are calculated by CasaXPS using a Monte Carlo method for determining the error distribution for the computed areas.

ACKNOWLEDGMENTS

This work was carried out in the Frederick Seitz Materials Research Laboratory Central Research Facilities, University of Illinois. E.B. and L.W.M. acknowledge support from the National Science Foundation under grants DMR - 1124696 and DMR - 1451219.

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SPECTRAL FEATURES TABLE

Spectrum ID #	Element/Transition	Peak Energy (eV)	Peak Width FWHM (eV)	Peak Area (eV × cts/s)	Sensitivity Factor	Concentration (at. %)	Peak Assignment
01314-02	Ga 2p _{3/2}	1117.3	1.42	NdGaO ₃
01314-02	Ga 2p _{3/2}	1121.1	2.15	NdGaO ₃
01314-02	Ga 2p _{1/2}	1144.1	1.42	NdGaO ₃
01314-02	Ga 2p _{1/2}	1147.9	2.15	NdGaO ₃
01314-03	O KL ₂₃ LL ₂₃	973.5
01314-03	O KL ₁ LL ₂₃	994.5
01314-03	O KL ₁ LL ₁	1008.7
01314-03	Nd 3d _{5/2}	978.5	5.00	NdGaO ₃
01314-03	Nd 3d _{5/2}	982.3	2.81	NdGaO ₃
01314-03	Nd 3d _{3/2}	1001.1	5.00	NdGaO ₃
01314-03	Nd 3d _{3/2}	1004.9	3.23	NdGaO ₃
01314-04	O 1s	529.7	1.01	32136.8	0.780	37.15	NdGaO ₃
01314-04 ^a	O 1s	531.4	1.70	7189.5	0.780	8.31	hydroxide
01314-04 ^a	O 1s	532.6	1.70	1779.9	0.780	2.06	carbonate
01314-05 ^a	C 1s	285.0	1.33	3788.5	0.278	12.29	hydrocarbon
01314-05 ^a	C 1s	286.6	1.36	583.9	0.278	1.89	C-hydroxide
01314-05 ^a	C 1s	288.7	1.90	555.4	0.278	1.8	carbonate
01314-06 ^b	Nd 4p _{3/2}	226.7	3.88	NdGaO ₃
01314-06 ^b	Nd 4p _{3/2}	229.9	3.94	NdGaO ₃
01314-07	Ga 3s	160.3	2.17	NdGaO ₃
01314-08	Nd 4d	52701.7	2.457	19.34	...
01314-08 ^b	Nd 4d	119.5	5.10	NdGaO ₃
01314-08 ^b	Nd 4d	123.0	5.10	NdGaO ₃
01314-08	Ga 3p	20061.6	1.054	17.16	...
01314-08	Ga 3p _{3/2}	105.0	2.65	NdGaO ₃
01314-08	Ga 3p _{1/2}	108.5	2.65	NdGaO ₃
01314-09	Nd 5s	38.4	1.74	NdGaO ₃
01314-09	Nd 5s	40.3	2.00	NdGaO ₃
01314-09	O 2s	22.4	1.92	NdGaO ₃
01314-09 ^a	O 2s	24.1	1.80	hydroxide, carbonate
01314-09	Ga 3d	19.7	1.09	NdGaO ₃
01314-09	Nd 5p	18.5	1.91	NdGaO ₃
01314-09 ^c	valence band	8.6	2.21	NdGaO ₃
01314-09 ^d	valence band	6.5	2.00	NdGaO ₃
01314-09 ^e	valence band	4.7	1.76	NdGaO ₃
01314-09 ^f	valence band maximum	3.0	NdGaO ₃

^a Result of exposure to air

^b Estimated based on peak fitting

^c O 2p and Ga 4s (Refs. 14 and 15)

^d O 2p and Ga 4p (Refs. 14 and 15)

^e O 2p (Refs. 14 and 15)

^f The position of VBM was estimated by subtracting 1/2 of the full width at half maximum (FWHM) from the position of the maximum intensity at the VBM.

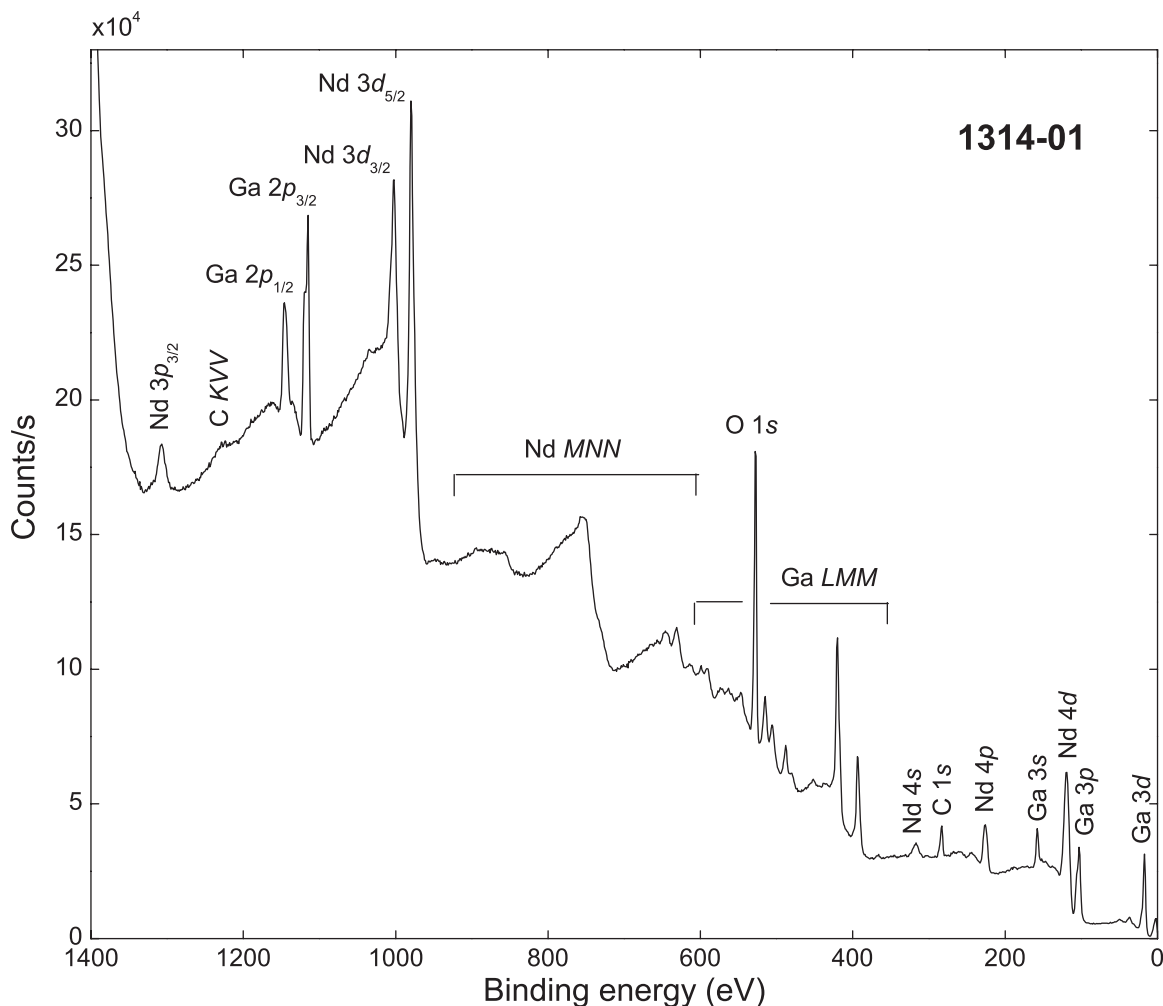
ANALYZER CALIBRATION TABLE

Spectrum ID #	Element/Transition	Peak Energy (eV)	Peak Width FWHM (eV)	Peak Area (eV × cts/s)	Sensitivity Factor	Concentration (at. %)	Peak Assignment
	Au 4f _{7/2}	84.0	0.72	151917.9
	Ag 3d _{5/2}	368.2	0.58	230506.2
	Cu 2p _{3/2}	932.6	0.88	410979.8

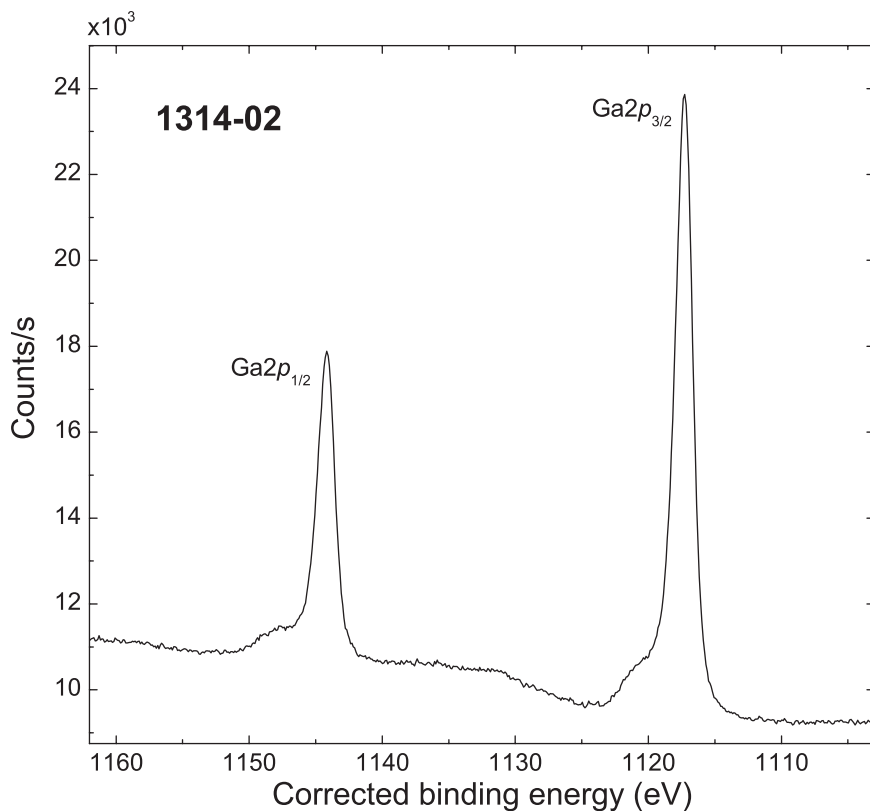
GUIDE TO FIGURES

Spectrum (Accession) #	Spectral Region	Voltage Shift*	Multiplier	Baseline	Comment #
1314-01	survey	0	1	0	
1314-02	Ga 2p	-2.071	1	0	
1314-03	Nd 3d	-2.071	1	0	
1314-04	O 1s	-2.071	1	0	
1314-05	C 1s	-2.071	1	0	
1314-06	Nd 4p _{3/2}	-2.071	1	0	
1314-07	Ga 3s	-2.071	1	0	
1314-08	Nd 4d, Ga 3p	-2.071	1	0	
1314-09	Nd 5s, O 2s, Ga 3d, Nd 5p, valence band	-2.071	1	0	

* Voltage shift of the archived (as-measured) spectrum relative to the printed figure. The figure reflects the recommended energy scale correction due to a calibration correction, sample charging, flood gun, or other phenomenon.

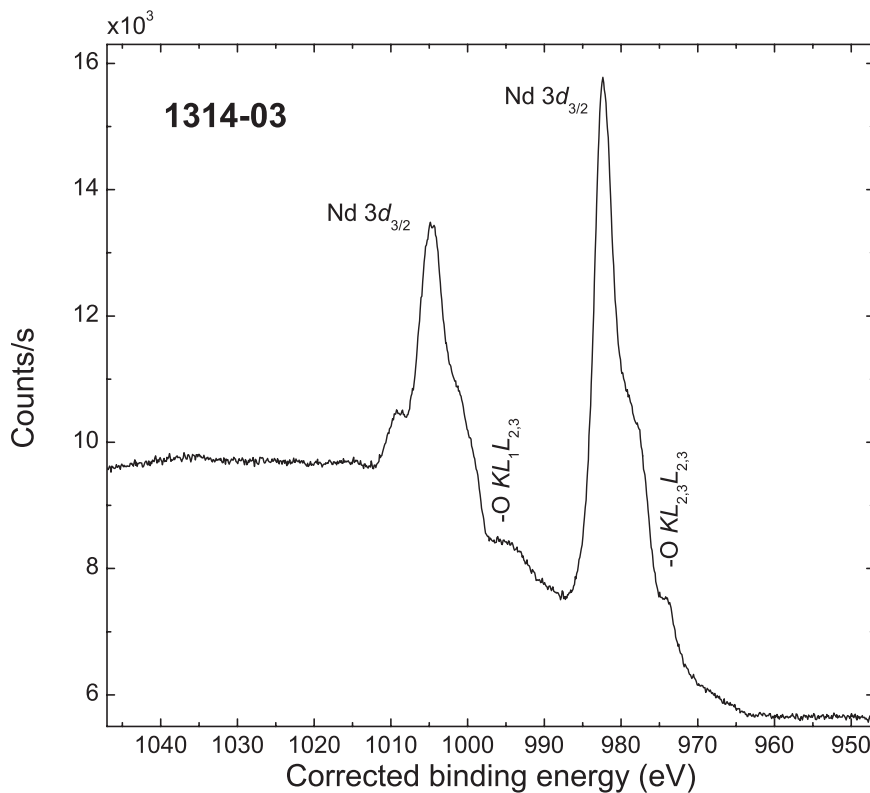


Accession #	01314-01
Host Material	Single crystal NdGaO ₃
Technique	XPS
Spectral Region	survey
Instrument	Kratos Axis Ultra
Excitation Source	Al K _α monochromatic
Source Energy	1486.6 eV
Source Strength	180 W
Source Size	2 mm × 2 mm
Analyzer Type	spherical sector
Incident Angle	54°
Emission Angle	0°
Analyzer Pass Energy:	160 eV
Analyzer Resolution	2.4 eV
Total Signal Accumulation Time	560 s
Total Elapsed Time	1120 s
Number of Scans	4
Effective Detector Width	33.6 eV



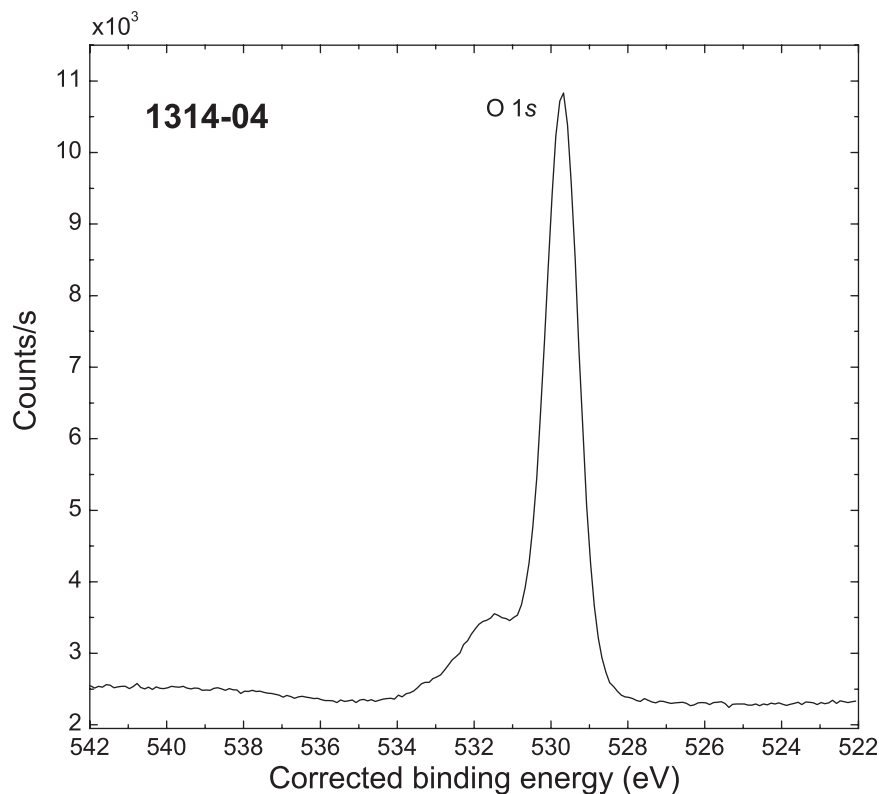
- Accession #: 01314-02
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Ga 2p

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 3606 s
 Total Elapsed Time: 9916.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



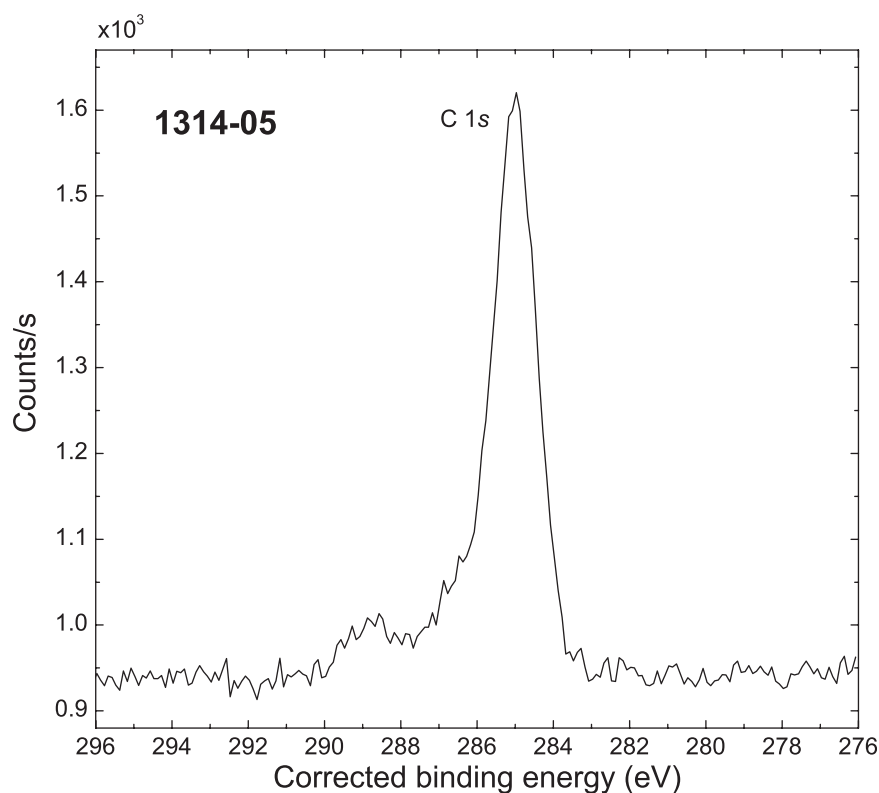
- Accession #: 01314-03
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Nd 3d

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 6006 s
 Total Elapsed Time: 16516.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



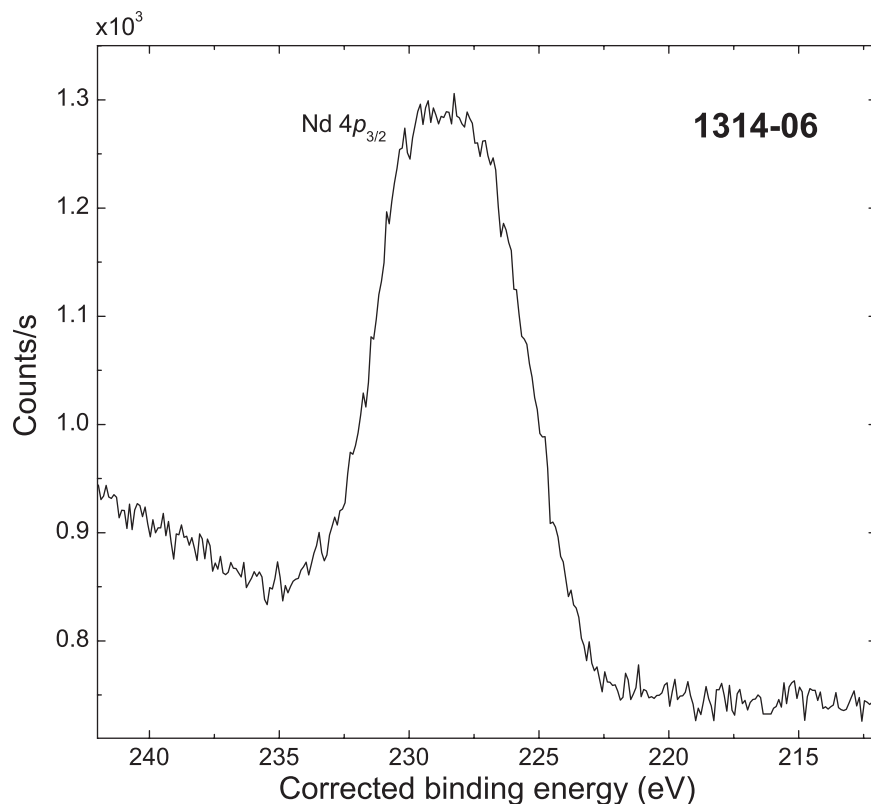
- Accession #: 01314-04
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: O 1s

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 1206 s
 Total Elapsed Time: 3316.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



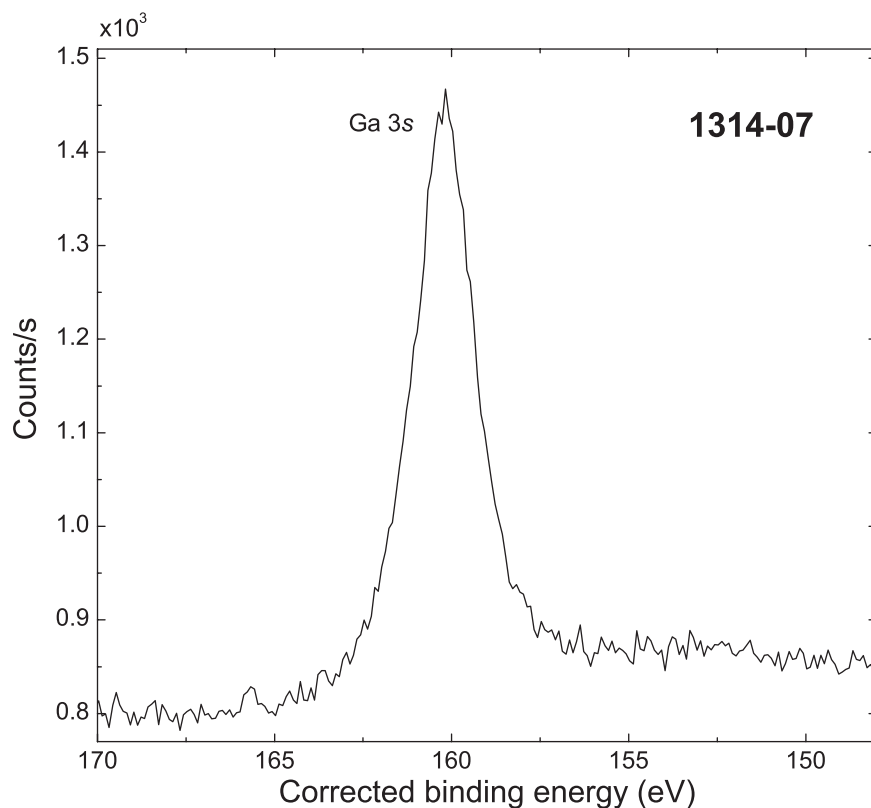
- Accession #: 01314-05
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: C 1s

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 1206 s
 Total Elapsed Time: 3316.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



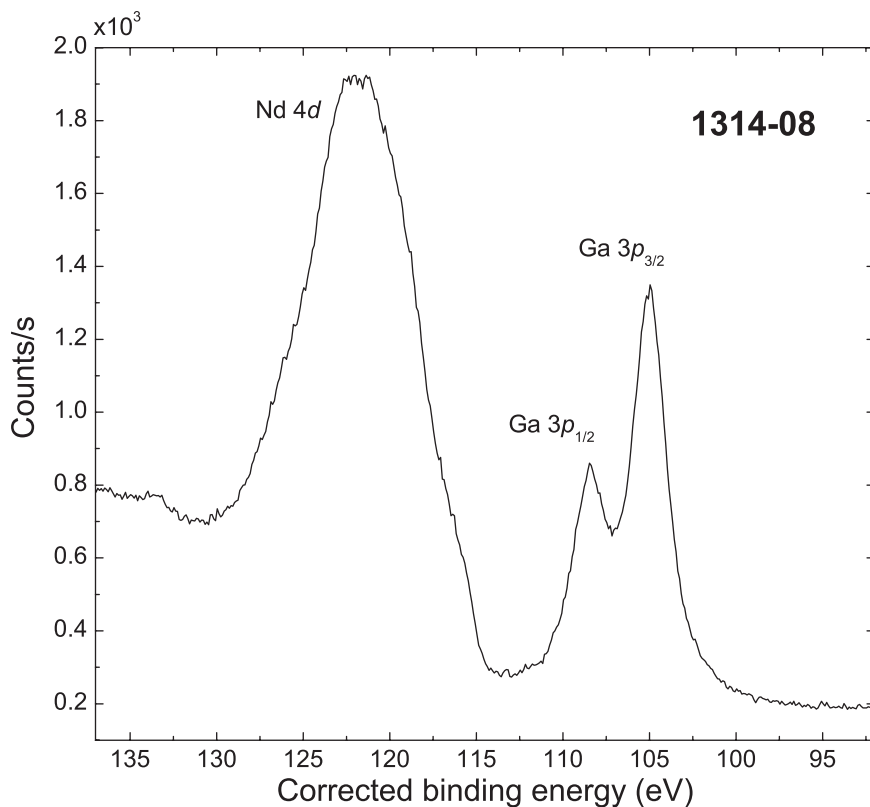
- Accession #: 01314-06
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Nd $4p_{3/2}$

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_{α} monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm \times 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 1806 s
 Total Elapsed Time: 4966.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



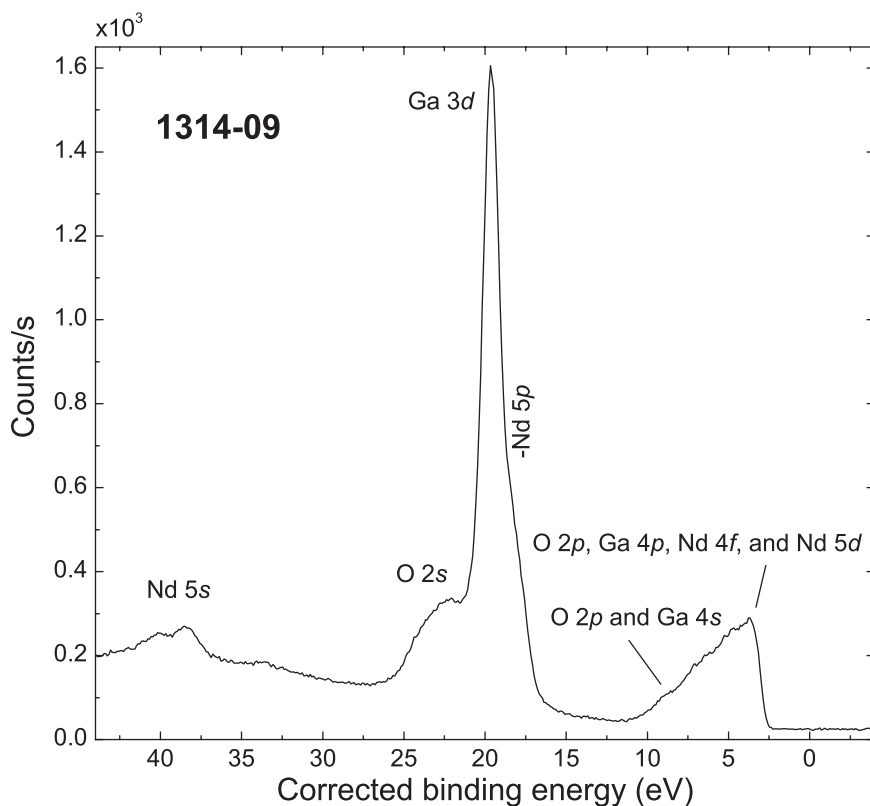
- Accession #: 01314-07
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Ga 3s

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_{α} monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm \times 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 1326 s
 Total Elapsed Time: 3646.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



- Accession #: 01314-08
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Nd 4d; Ga 3p

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 2706 s
 Total Elapsed Time: 7441.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV



- Accession #: 01314-09
- Host Material: Single crystal NdGaO₃
- Technique: XPS
- Spectral Region: Nd 5s; O 2s; Ga 3d; Nd 5p; valence band maximum

Instrument: Kratos Axis Ultra
 Excitation Source: Al K_α monochromatic
 Source Energy: 1486.6 eV
 Source Strength: 180 W
 Source Size: 2 mm × 2 mm
 Analyzer Type: spherical sector
 Incident Angle: 54°
 Emission Angle: 0°
 Analyzer Pass Energy: 20 eV
 Analyzer Resolution: 0.3 eV
 Total Signal Accumulation Time: 6734 s
 Total Elapsed Time: 18518.5 s
 Number of Scans: 20
 Effective Detector Width: 4.2 eV